TOSHIBA

GaAs IRED & PHOTO-THYRISTOR

Office Machine

Household Use Equipment

Solid State Relay

Switching Power Supply

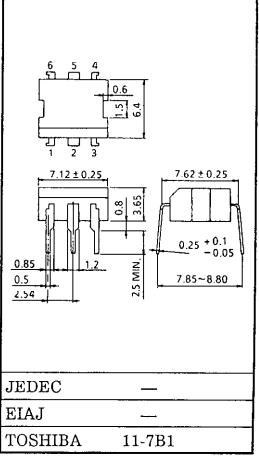
The Toshiba TLP741G consists of a photo-thyristor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

- Peak Off-State Voltage : 400V (Min.)
- Trigger LED Current : 10mA (Max.)
- On-State Current : 150mA (Max.)
- Isolation Voltage : 4000V_{rms}(Min.)
- Guaranteed Requirements of IEC380/VDE0806
- Climatic Test Class
- Isolation Creepage Path : 8.2mm (Min.)
 - : 7.6mm (Min.)

: 55/150/21

: Group I^{*2}

- Isolation ClearanceIsolation Operating Voltage
- : $500V_{ac}$ or $600V_{dc}$ for : Isolation Group C. ^{*1}
- Creeping Current Resistance :
- TUV Approved for DIN57883/VDE0883/6.80
 *1: According to VDE0110, Table 4
 *2. According to VDE0110, Table 2
 - *2: According to VDE0110, Table 3



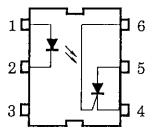
Weight: 0.4g

Supplementary Information

Lead Form Options

Tape and Reel

Pin Configuration (Top View)



- 1 : ANODE
- 2 : CATHODE
- 3 : NC
- 4 : CATHODE
- 5 : ANODE
- 6 : GATE

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Unit in mm

	CHARACTERISTIC	SYMBOL	RATING	UNIT
	Forward Current	I _F	60	mA
	Forward Current Derating (Ta \ge 39°C)	∆I _F /°C	-0.7	mA/°C
	Peak Forward Current (100µs pulse, 100pps)	I _{PF}	1	А
LED	Power Dissipation	PD	60 -0.7 1 100 -1.0 5 125 400 400 30 2 5 150 -2.0 3 2 5 150 -2.0 3 2 5 150 -2.0 3 2 5 150 -2.0 3 2 5 150 -2.0 100 -55~150 -55~150 260 250	mW
	Power Dissipation Derating (Ta $\ge 25^{\circ}$ C)	$\begin{tabular}{ c c c c c } \hline I_F & G0 \\ \hline I_a \ge 39^\circ C) & \Delta I_F/^\circ C & -0.7 \\ \hline $	-1.0	mW/°C
ED	Reverse Voltage	V _R	5	V
	Junction Temperature	Тј	125	°C
	Peak Forward Voltage ($R_{GK} = 27k\Omega$)	V _{DRM}	400	V
	Peak Reverse Voltage ($R_{GK} = 27k\Omega$)	V _{RRM}	400	V
	On-State Current	I _{T(RMS)}	150	mA
	On-State Current Derating (Ta \ge 25°C)	ΔI _T /°C	-2.0	mA/°C
	Peak On-State Current (100µs pulse, 120pps)	I _{TP}	3	А
DETECTOR	Peak One Cycle Surge Current	I _{TSM}	2	А
	Peak Reverse Gate Voltage	V _{GM}	5	V
	Power Dissipation	PD	150	mW
	Power Dissipation Derating (Ta $\ge 25^{\circ}$ C)	∆P _D /°C	-2.0	mW/°C
	Junction Temperature	Тj	100	°C
Storage Tempe	erature Range	T _{stg}	-55~150	°C
Operating Tem	perature Range		-55~100	°C
Lead Soldering	Temperature (10s)	T _{sol}	260	°C
Total Package	Power Dissipation	PT	250	mW
Total Package	Power Dissipation Derating (Ta \ge 25°C)	∆P _T /°C	-3.3	mW/°C
Isolation Voltag	je (AC, 1 min., R.H. ≤ 60%)	BVS	4000	Vrms

Individual Electrical Characteristics (Ta = 25°C)

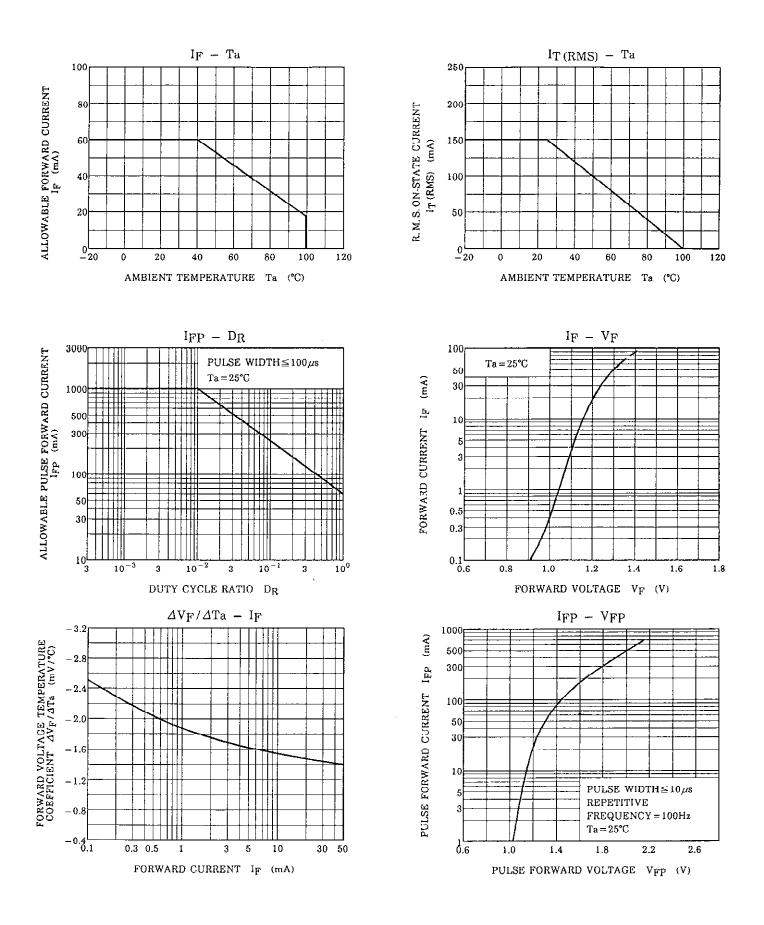
CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN.	TYP.	MX.	UNIT
	Forward Voltage	V _F	I _F = 10mA		1.0	1.15	1.3	V
LED	Reverse Current	I _R	$V_{R} = 5V$		_	-	10	μA
	Capacitance	CT	V = 0, f = 1MHz		_	30	-	pF
DETECTOR	Off-State Current	I _{DRM}	$V_{AK} = 400V$ $R_{GK} = 27k\Omega$	Ta = 25°C	-	10	5000	nA
				Ta = 100°C	-	1	100	μA
	Reverse Current	I _{RRM}	$V_{KA} = 400V$ $R_{GK} = 27k\Omega$	Ta = 25°C	-	10	5000	nA
				Ta = 100°C	-	1	100	μA
	On-State Voltage	V _{TM}	I _{TM} = 100mA		-	0.9	1.3	V
	Holding Current	Ι _Η	$R_{GK} = 27k\Omega$		-	0.2	-	mA
	Off-State dv/dt	dv/dt	$V_D = 280V, R_{GK} = 27k\Omega$		5	10	-	V/µs
	Capacitance C _j	C _j V =	V = 0, f = 1MHz Anode to Gate		-	20	-	ъE
			G	ate to Cathode	-	350	-	– pF

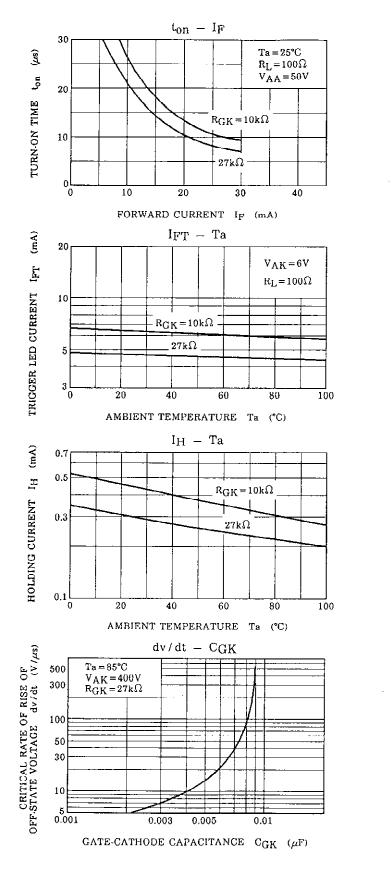
Coupled Characteristics (Ta = 25°C)

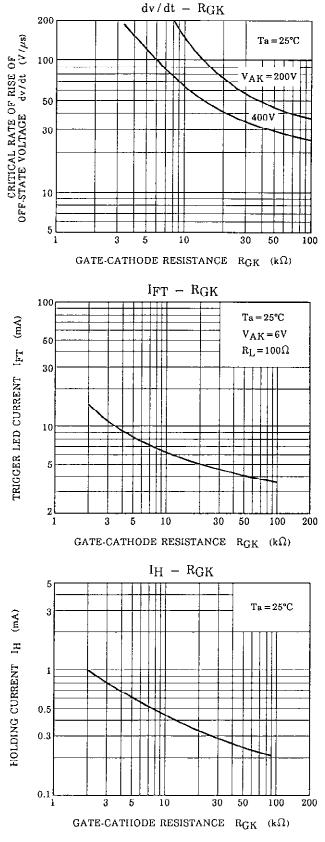
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MX.	UNIT	
Trigger LED Current	I _{FT}	V_{AK} = 6V, R_{GK} = 27k Ω	-	4	10	mA	
Turn-on Time	t _{on}	$I_{F} = 30 \text{mA}, V_{AA} = 50 \text{V}, \\ R_{GK} = 27 \text{k}\Omega$	-	10	_	μs	
Coupled dv/dt	dv/dt	$V_{S} = 500V, R_{GK} = 27k\Omega$	500	-	_	V/µs	
Capacitance (Input to Output)	C _S	V _S = 0, f = 1MHz	_	0.8	_	pF	
Isolation Resistance	R _S	V _S = 500V	5 x 10 ¹⁰	10 ¹⁴	_	Ω	
		AC, 1 minute	4000	-	_	V	
Isolation Voltage	oltage BV _S	AC, 1 second, in oil	_	10000	_	V _{rms}	
		DC, 1 minute, in oil	-	10000	_	V _{dc}	

Recommended Operating Conditions

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MX.	UNIT
Supply Voltage	V _{AC}	_	_	120	V _{ac}
Forward Current	١ _F	15	20	25	mA
Operating Temperature	T _{opr}	-25	_	85	°C
Gate to Cathode Resistance	R _{GK}	-	27	33	kΩ
Gate to Cathode Capacity	C _{GK}	_	0.01	0.1	μF







Notes